

REMARKS

Claims 1-14 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Applicant's Related Art FIGs. 2 and 3F (hereinafter "APAF") in view of U.S. Patent No. 5,162,933 (hereinafter "Kakuda") and U.S. Patent No. 5,825,437 (hereinafter "Seo"). Applicant respectfully traverses the rejection as being based upon Applicant's Related Art and a reference that neither teach nor suggest the novel combination of features recited by independent claim 1, and hence dependent claims 2-14.

With respect to independent claim 1, Applicant respectfully submits that neither of APAF nor Kakuda disclose a claimed combination comprising at least feature of "a plurality of thin film transistors formed on the substrate adjacent to intersections of the gate lines and the data lines, each thin film transistor including a gate electrode, a gate insulation layer, an active layer, an ohmic contact layer, a source electrode, and a drain electrode, the source electrode extended from each of the data lines and overlapping a portion of the gate electrode", "a metal layer formed on an entire surface of each of the data lines and an entire surface of the source electrode, and at peripheral portions of the drain electrode" and "wherein the source electrode is positioned between the ohmic contact layer and the metal layer."

The Office Action admits that AFPA and Kakuda show all of the elements of the claims except the metal layer formed on an entire surface of the source electrode. Accordingly, the Office Action relies upon Seo for allegedly showing (fig. 8d, 8e) that a source side electrode (7 on the left side) has a metal layer (8) formed on its entire surface. Applicant respectfully disagrees.

The source side electrode (7 on the left side) in Seo can not correspond to a source electrode in the claimed invention. Referring to figure 8d and line 65 in column 7 to line'7 in

column 8 of Seo, a source side electrode (7 on the left side) is a patterned doped semiconductor layer 7. In the disclosure of Seo, after sequentially depositing a semiconductor layer and a doped semiconductor layer on first insulating layer 5, a patterned semiconductor layer 6 and a patterned doped semiconductor layer 7 are photolithographically patterned on first insulating layer 5. Then, a third metal layer of the source/drain electrodes is formed on doped semiconductor layer 7. Namely, Seo does not show a metal layer formed on the entire surface of the source electrode, but a source electrode formed on the entire surface of an ohmic contact layer. None of the cited references remedy the deficient teachings of Seo.

For at least the above reasons, Applicant respectfully submits that claims 1-14 are neither taught nor suggested by APAF and/or Kakuda, whether taken alone or in combination. Thus, Applicant respectfully asserts that the rejections under 35 U.S.C. § 103(a) should be withdrawn because the above-discussed novel combination of features are neither taught nor suggested by any of the applied references.

CONCLUSION

In view of the foregoing, Applicant respectfully requests reconsideration and the timely allowance of the pending claims. Should the Examiner feel that there are any issues outstanding after consideration of the Response, the Examiner is invited to contact the Applicant's undersigned representative to expedite prosecution.

EXCEPT for issue fees payable under 37 C.F.R. § 1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. §§ 1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account No.

50-0310. This paragraph is intended to be a **CONSTRUCTIVE PETITION FOR
EXTENSION OF TIME** in accordance with 37 C.F.R. § 1.136(a)(3).

Respectfully submitted,

Morgan, Lewis & Bockius LLP

Dated: June 15, 2009

By: Mary Jane Boswell
Mary Jane Boswell, Reg. No. 33,652

Customer No. 009629
Morgan, Lewis & Bockius LLP
1111 Pennsylvania Avenue, N.W.
Washington, D.C. 20004
Tel: 202-739-3000
Fax: 202-739-3001